# BLC9G24XS-170AV

# **Power LDMOS transistor**

**AMPLEON** 

Rev. 2 — 20 December 2016

**Product data sheet** 

### 1. Product profile

### 1.1 General description

170 W LDMOS packaged asymmetrical Doherty power transistor for base station applications at frequencies from 2300 MHz to 2400 MHz.

Table 1. Typical performance

Typical RF performance at  $T_{case}$  = 25 °C in the Doherty demo board.

Test signal	f	V <sub>DS</sub>	P <sub>L(AV)</sub>	G <sub>p</sub>	$\eta_D$	ACPR
	(MHz)	(V)	(W)	(dB)	(%)	(dBc)
1-carrier W-CDMA	2300 to 2400	30	28	15.5	47	-30 <sup>[1]</sup>

<sup>[1]</sup> Test signal: 3GPP test model 1; 1 to 64 DPCH; PAR = 7.2 dB at 0.01 % probability on CCDF.

#### 1.2 Features and benefits

- Excellent ruggedness
- High efficiency
- Low thermal resistance providing excellent thermal stability
- Decoupling leads to enable improved video bandwidth
- Lower output capacitance for improved performance in Doherty applications
- Designed for low memory effects providing excellent pre-distortability
- Internally matched for ease of use
- Integrated ESD protection
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

RF power amplifier for W-CDMA base stations and multi carrier applications in the 2300 MHz to 2400 MHz frequency range

### 2. Pinning information

Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
1	drain1 (main)			
2	drain2 (peak)			1, 5
3	gate1 (main)			3_
4	gate2 (peak)		7	7
5	video decoupling (main)			4 4
6	video decoupling (peak)		3 4	2, 6
7	source	[1]		aaa-007731

<sup>[1]</sup> Connected to flange.

### 3. Ordering information

Table 3. Ordering information

Type number	Packag	ackage					
	Name	Description	Version				
BLC9G24XS-170AV	-	air cavity plastic earless flanged package; 6 leads	SOT1275-3				

### 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	65	V
$V_{GS}$	gate-source voltage		-0.5	+13	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature	[1]	-	225	°C

Continuous use at maximum temperature will affect the reliability, for details refer to the online MTF calculator.

### 5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{\text{th(j-case)}}$	thermal resistance from junction to case	$T_{case}$ = 80 °C; $I_{Dq}$ = 100 mA; $V_{GS(amp)\ peak}$ = 1 V		
		P <sub>L</sub> = 28 W	0.247	K/W
		P <sub>L</sub> = 44.5 W	0.197	K/W

### 6. Characteristics

Table 6. DC characteristics

 $T_i$  = 25 °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit				
Main device										
V <sub>(BR)DS</sub> s	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.6 \text{mA}$	65	-	76.5	V				
$V_{GS(th)}$	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 60 mA	1.5	2.0	2.5	V				
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 300 mA	1.65	2.15	2.65	V				
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	1.4	μΑ				
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	12.1	-	Α				
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA				
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 3000 mA	-	4.56	-	S				
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 2.1 \text{ A}$	-	237.5	385	mΩ				
Peak dev	vice									
V <sub>(BR)DS</sub> s	drain-source breakdown voltage	$V_{GS} = 0 \text{ V}; I_D = 0.9 \text{ mA}$	65	-	76.5	V				
$V_{GS(th)}$	gate-source threshold voltage	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 90 mA	1.5	2.0	2.5	V				
$V_{GSq}$	gate-source quiescent voltage	V <sub>DS</sub> = 28 V; I <sub>D</sub> = 450 mA	1.65	2.15	2.65	V				
I <sub>DSS</sub>	drain leakage current	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 32 V	-	-	1.4	μΑ				
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $V_{DS} = 10 \text{ V}$	-	17.9	-	Α				
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 11 V; V <sub>DS</sub> = 0 V	-	-	140	nA				
g <sub>fs</sub>	forward transconductance	V <sub>DS</sub> = 10 V; I <sub>D</sub> = 4500 mA	-	6.72	-	S				
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 3.15 \text{ A}$	-	158	260	mΩ				

#### Table 7. RF characteristics

Test signal: 1-carrier W-CDMA; PAR = 7.2 dB at 0.01 % probability on the CCDF; 3GPP test model 1; 1 to 64 DPCH;  $f_1$  = 2300 MHz;  $f_2$  = 2400 MHz; RF performance at  $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main);  $V_{GS(amp)peak}$  = 0.65 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2300 MHz to 2400 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Gp	power gain	P <sub>L(AV)</sub> = 28 W	14.3	15.5	-	dB
RLin	input return loss	P <sub>L(AV)</sub> = 28 W	-	-10	<b>-6</b>	dB
$\eta_{D}$	drain efficiency	P <sub>L(AV)</sub> = 28 W	40	45	-	%
ACPR	adjacent channel power ratio	P <sub>L(AV)</sub> = 28 W	-	-29	-24	dBc

#### Table 8. RF characteristics

Test signal: pulsed CW;  $t_p$  = 100  $\mu$ s;  $\delta$  = 10 %; f = 2400 MHz; RF performance at  $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main);  $V_{GS(amp)peak}$  = 0.65 V;  $T_{case}$  = 25 °C; unless otherwise specified; in an asymmetrical Doherty production test circuit at frequencies from 2300 MHz to 2400 MHz.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
P <sub>L(3dB)</sub>	output power at 3 dB gain compression		134	157	-	W

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### 7. Test information

#### 7.1 Ruggedness in Doherty operation

The BLC9G24XS-170AV is capable of withstanding a load mismatch corresponding to a VSWR = 10 : 1 through all phases under the following conditions:  $V_{DS}$  = 30 V;  $I_{Dq}$  = 150 mA (main);  $V_{GS(amp)peak}$  = 0.7 V;  $P_L$  = 110 W (CW); f = 2300 MHz.

### 7.2 Impedance information

Table 9. Typical impedance of main device

Measured load-pull data of main device;  $I_{Dq} = 300 \text{ mA (main)}$ ;  $V_{DS} = 30 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum pov	Maximum power load									
2300	3.1 – j10.0	3.5 – j6.7	88	58.6	17.8					
2350	3.8 – j8.5	3.0 – j6.8	87	57.1	18.1					
2400	8.3 – j11.9	3.2 – j6.7	87	57.4	18.2					
Maximum dra	in efficiency load									
2300	3.1 – j10.0	6.0 – j5.2	61	66	19.5					
2350	3.8 – j8.5	4.9 – j4.7	62	65.4	20.2					
2400	8.3 – j11.9	5.2 – j4.3	63	64	20.4					

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in Figure 1.

Table 10. Typical impedance of peak device

Measured load-pull data of peak device;  $I_{Dq}$  = 540 mA (peak);  $V_{DS}$  = 30 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [2]	G <sub>p</sub> [2]					
(MHz)	(Ω)	(Ω)	(W)	(%)	(dB)					
Maximum	Maximum power load									
2300	4.2 – j11.2	4.5 – j6.4	124	58.7	18.3					
2350	6.1 – j10.7	4.0 – j6.7	126	58.7	17.8					
2400	8.2 – j13.7	3.8 – j6.4	119	57.5	18.2					
Maximum	drain efficiency loa	ad	·							
2300	4.2 – j11.2	3.8 – j3.7	102	66	19.7					
2350	6.1 – j10.7	3.7 – j4.4	104	65	19.6					
2400	8.2 – j13.7	3.2 – j4.3	94	64	19.8					

<sup>[1]</sup>  $Z_S$  and  $Z_L$  defined in <u>Figure 1</u>.

<sup>[2]</sup> at 3 dB gain compression.

<sup>[2]</sup> at 3 dB gain compression.

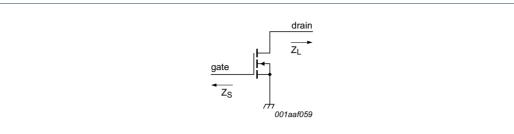


Fig 1. Definition of transistor impedance

### 7.3 Recommended impedances for Doherty design

Table 11. Typical impedance of main device at 1 : 1 load Measured load-pull data of main device;  $I_{Dq} = 300 \text{ mA (main)}$ ;  $V_{DS} = 30 \text{ V}$ .

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2300	3.1 – j10.0	4.0 – j5.9	49.2	37.0	18.2
2350	3.8 – j8.5	3.8 – j6.2	49.3	38.0	18.8
2400	8.3 – j11.9	4.0 – j6.3	49.2	38.8	19.0

- [1] Z<sub>S</sub> and Z<sub>L</sub> defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 44.5 \text{ dBm}$ .

Table 12. Typical impedance of main device at 1 : 2.5 load

Measured load-pull data of main device;  $I_{Dq}$  = 300 mA (main);  $V_{DS}$  = 30 V.

f	Z <sub>S</sub> [1]	Z <sub>L</sub> [1]	P <sub>L</sub> [2]	η <sub>D</sub> [3]	G <sub>p</sub> [3]
(MHz)	(Ω)	(Ω)	(dBm)	(%)	(dB)
2300	3.1 – j10.0	6.1 – j2.7	47.3	50.1	19.8
2350	3.8 – j8.5	5.5 – j3.4	47.5	50.0	20.5
2400	8.3 – j11.9	4.7 – j2.9	47.3	51.0	20.5

- [1]  $Z_S$  and  $Z_L$  defined in Figure 1.
- [2] at 3 dB gain compression.
- [3] at  $P_{L(AV)} = 44.5 \text{ dBm}$ .

### 7.4 VBW in Doherty operation

The BLC9G24XS-170AV shows 100 MHz (typical) video bandwidth in Doherty demo board in 2350 MHz at  $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA and  $V_{GS(amp)peak}$  = 0.8 V.

#### 7.5 Test circuit

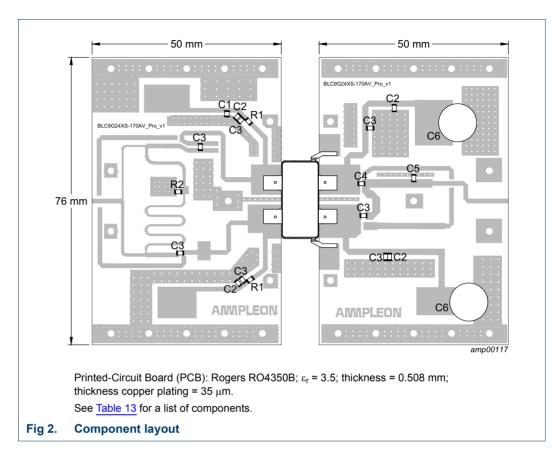


Table 13. List of components

See Figure 2 for component layout.

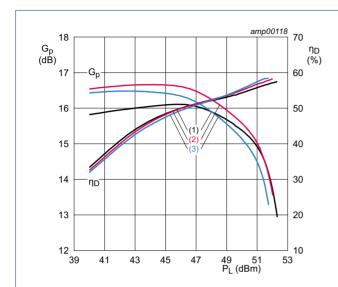
Component	Description	Value	Remarks
C1	multilayer ceramic chip capacitor	1 μF, 50 V [1]	Murata
C2	multilayer ceramic chip capacitor	10 μF, 50 V [1]	Murata
C3	multilayer ceramic chip capacitor	11 pF [2]	ATC 600F
C4	multilayer ceramic chip capacitor	8.2 pF [2]	ATC 600F
C5	multilayer ceramic chip capacitor	0.2 pF [2]	ATC 600F
C6	electrolytic capacitor	1000 μF, 100 V	
R1	resistor	5.1 Ω	SMD 0805
R2, R3	resistor	50 Ω	SMD 0805

<sup>[1]</sup> Murata or capacitor of same quality

[2] American Technical Ceramics type 600F or capacitor of same quality

### 7.6 Graphical data

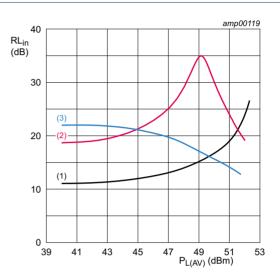
### 7.6.1 CW



 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 3. Power gain and drain efficiency as function of output power; typical values

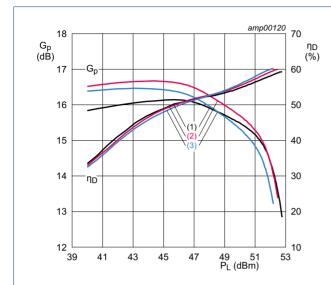


 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 4. Input return loss as a function of average output power; typical values

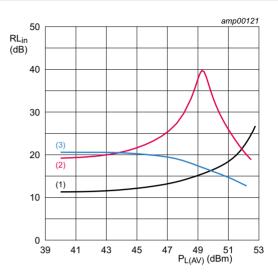
#### 7.6.2 Pulsed CW



 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 5. Power gain and drain efficiency as function of output power; typical values

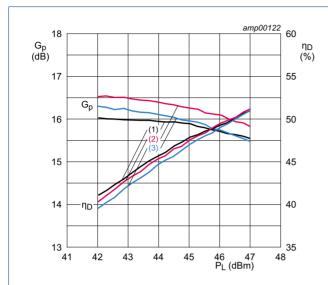


 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 6. Input return loss as a function of average output power; typical values

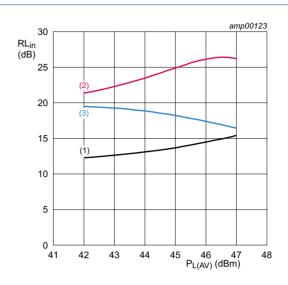
#### 7.6.3 1-Carrier W-CDMA



 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

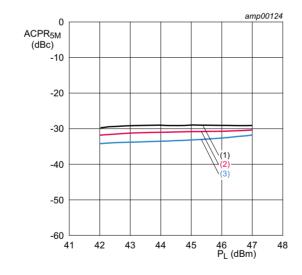
Fig 7. Power gain and drain efficiency as function of output power; typical values



 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 8. Input return loss as a function of average output power; typical values

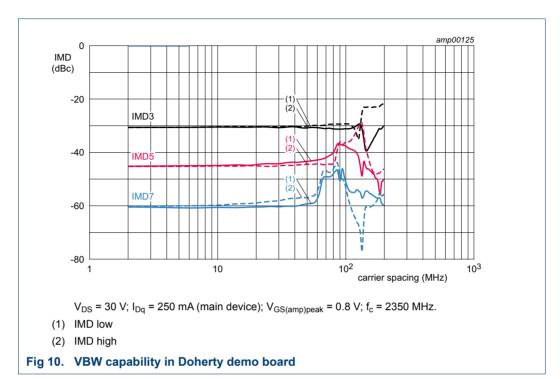


 $V_{DS}$  = 30 V;  $I_{Dq}$  = 250 mA (main device);  $V_{GS(amp)peak}$  = 0.65 V.

- (1) f = 2300 MHz
- (2) f = 2350 MHz
- (3) f = 2400 MHz

Fig 9. Adjacent channel power ratio (5 MHz) as a function of output power; typical values

#### 7.6.4 2-Tone VBW



### 8. Package outline

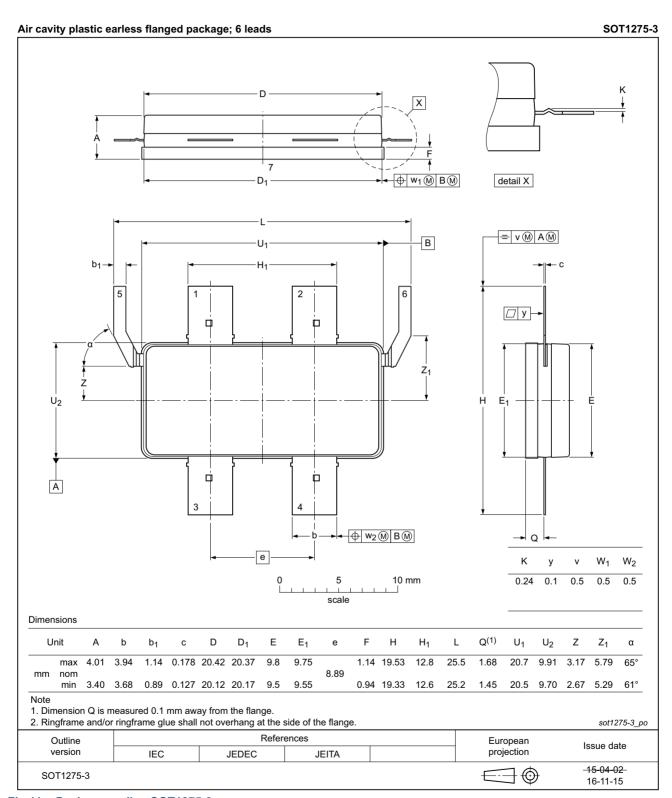


Fig 11. Package outline SOT1275-3

### 9. Handling information

#### **CAUTION**



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

Table 14. ESD sensitivity

ESD model	Class
Charged Device Model (CDM); According to ANSI/ESDA/JEDEC standard JS-002	C2A [1]
Human Body Model (HBM); According to ANSI/ESDA/JEDEC standard JS-001	2 [2]

<sup>[1]</sup> CDM classification C2A is granted to any part that passes after exposure to an ESD pulse of 500 V, but fails after exposure to an ESD pulse of 750 V.

### 10. Abbreviations

Table 15. Abbreviations

Acronym	Description
3GPP	3rd Generation Partnership Project
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
DPCH	Dedicated Physical CHannel
ESD	ElectroStatic Discharge
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
MTF	Median Time to Failure
PAR	Peak-to-Average Ratio
SMD	Surface Mounted Device
VBW	Video BandWidth
VSWR	Voltage Standing Wave Ratio
W-CDMA	Wideband Code Division Multiple Access

## 11. Revision history

Table 16. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BLC9G24XS-170AV v.2	20161220	Product data sheet	-	BLC9G24XS-170AV v.1
Modifications:	Figure 11 on page 11: updated package outline drawing SOT1275-3			
	Section 9 on page 12: updated Handling information			
BLC9G24XS-170AV v.1	20161021	Product data sheet	-	-

<sup>[2]</sup> HBM classification 2 is granted to any part that passes after exposure to an ESD pulse of 2000 V, but fails after exposure to an ESD pulse of 4000 V.

### 12. Legal information

#### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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## BLC9G24XS-170AV

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### 13. Contact information

For more information, please visit: http://www.ampleon.com

For sales office addresses, please visit: http://www.ampleon.com/sales

# **AMPLEON**

# BLC9G24XS-170AV

#### **Power LDMOS transistor**

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